SiT7601

Endura™ Ruggedized MHz Silicon MEMS Oscillator

Features

- 46 fixed frequencies between 4 MHz and 125 MHz
- Industry best *g*-sensitivity of 0.01 ppb/*g*
- ±30 ppm frequency stability over -40°C to 105°C
- ±50 ppm frequency stability over -55°C to 125°C
- Supply voltage options: 1.5 V, 1.8 V, 2.5 V and 3.3 V
- 2.5 mA low power consumption
- LVCMOS compatible output
- 1 µA standby current
- 450 fs RMS phase jitter
- Industry-standard packages: 2.0 x 1.6, 2.5 x 2.0, 3.2 x 2.5 mm
- RoHS and REACH compliant, Lead-free, Halogen-free and Antimony-free

Applications

- Avionics
- Precision Guided Kits
- Sensors
- Cameras and video equipment
- FPGA clocking
- Asset tracking systems
- Engine control
- Shock and vibration environments
- Aerospace and military applications

Order samples

Electrical Specifications

Table 1. Electrical Characteristics

All Min and Max limits are specified over temperature for all supply voltages with 15 pF output load in air unless otherwise stated. Typical values are specified at 25°C and at the nominal value of the highest voltage option for that parameter.

Parameters	Symbol	Min.	Typ.	Max.	Unit	Condition
Frequency Range						
Fixed Frequency Options	f	5, 10, 14.74056, 16.9362, 20, 25, 31.25, 33.333333, 50, 62.5, 78.125, 100, 125			MHz	SiT7601A
		4, 4.096, 6, 8, 8.192, 9, 12, 16, 18, 18.432, 19.2, 24, 24.576, 30.72, 32, 32.768, 36, 38.4, 48, 61.44, 64, 72, 76.8, 96, 122.88				SiT7601B
		7, 13, 21, 27, 39, 63, 91, 117				SiT7601C
Frequency Stability and Aging						
Frequency Stability Over Temperature	F_stab	-50	–	+50	ppm	Supported for -55°C to 125°C, -40°C to 125°C temp range options. Inclusive of Initial tolerance at 25°C, 1st year aging at 25°C, and variations over operating temperature, rated power supply voltage and load (15 pF ±10%).
		-30	–	+30		Supported for -40°C to 105°C Inclusive of Initial tolerance at 25°C, 1st year aging at 25°C, and variations over operating temperature, rated power supply voltage and load (15 pF ±10%).
		-25	–	+25		Supported over -40ºC to +85ºC temp range, within -40°C to +105°C temp range
1-year aging	F_1y	–	–	±225	ppb	Tested at 85ºC. Guaranteed by design and characterization.
5-year aging	F_5y	–	–	±250		
10-year aging	F_10y	–	–	±270		
20-year aging	F_20y	–	–	±300		
G-Sensitivity	F_sens	–	0.01	–	ppb/*g*	Low sensitivity grade; total gamma over 3 axes; 15 Hz to 2 kHz; MIL-PRF-55310, computed per section 4.8.18.3.1
Operating Temperature Range						
Operating Temperature Range	T_use	-40	–	+105	°C	Extended Industrial
		-40	–	+125		Extended Automotive
		-55	–	+125		Mil-Aero

Table 1. Electrical Characteristics (continued)

Parameters	Symbol	Min.	Typ.	Max.	Unit	Condition
Supply Voltage and Current Consumption						
Supply Voltage	Vdd	1.35	1.5	1.65	V	"15"
		1.62	1.8	1.98		"18"
		2.25	2.5	2.75		"25"
		2.97	3.3	3.63		"33"
		1.62	-	3.63		"YY"
Current Consumption	Idd	–	2.5	4.0	mA	f = 27 MHz, no load, 1.5 V, 1.8 V
		–	2.7	4.0	mA	f = 27 MHz, no load, 2.5 V, 3.3 V
Standby Current	I_std	–	0.15	1.2	µA	Up to 125°C, $\overline{ST}$ = 0
Mid-Standby Current	I_midstd	–	0.33	0.75	mA	Up to 125°C, $\overline{MS}$ = 0
LVCMOS Characteristics						
Duty Cycle	DC	48	–	52	%	All Vdd levels
Rise/Fall Time	T_R/T_F	–	–	1.9	ns	Vdd = 1.62 V – 3.63 V, 20% - 80%, 5-15 pF Load, f = 27 MHz
		–	–	2.5		Vdd = 1.35 V – 1.65 V, 20% - 80%, 15 pF Load, f = 27 MHz
Output High Voltage	VOH	90%	–	–	Vdd	IOL = -4 mA (Vdd = 3.3 V) IOL = -3 mA (Vdd = 2.5 V) IOL = -2 mA (Vdd = 1.8 V) IOL = -1.5 mA (Vdd = 1.5 V)
Output Low Voltage	VOL	–	–	10%	Vdd	IOL = 4 mA (Vdd = 3.3 V) IOL = 3 mA (Vdd = 2.5 V) IOL = 2 mA (Vdd = 1.8 V) IOL = 1.5 mA (Vdd = 1.5 V)
Input Characteristics						
Input High Voltage	VIH	70%	–	–	Vdd	Pin 1, OE or $\overline{ST}$ or $\overline{MS}$
Input Low Voltage	VIL	–	–	30%	Vdd	Pin 1, OE or $\overline{ST}$ or $\overline{MS}$
Input Pull-down Impedance	VIH	2	–	–	MΩ	Pin 1, OE, $\overline{ST}$ or $\overline{MS}$ or NC
Start-up and Resume Time						
Startup Time	T_start	–	0.7	1	ms	Measured from the time Vdd reaches its rated minimum value
Enable/Disable Time	T_oe	–	-	150	ns	f = 27 MHz. For other frequencies, T_oe = 100 ns + 3*cycles.
Resume Time (Standby)	T_resume	–	0.5	0.7	ms	
Resume Time (Mid-Standby)		–	0.1	0.11	ms	
Jitter and Phase Noise						
RMS Period Jitter[1]	T_jitt	–	1	1.2	ps	f = 27 MHz, 10K cycles
RMS Phase Jitter (random)[2]	T_phj	–	0.45	0.70	ps	f = 27 MHz, 12 kHz – 20 MHz integration bandwidth, phase noise measured 12 kHz – 10 MHz and extended flat above 10 MHz
		–	0.33	0.625	ps	f = 27 MHz, 12 kHz – 5 MHz integration bandwidth, phase noise measured 12 kHz – 5 MHz
		–	0.42	0.70	ps	f = 48 MHz, 12 kHz – 20 MHz integration bandwidth, phase noise measured 12 kHz – 20 MHz
Phase Noise	PN	–	-145	–	dBc/Hz	f = 27 MHz, f_offset = 100 kHz
Spurious Phase Noise	T_spn	–	-85	–	dBc	f = 27 MHz, 1.8 V, 12 kHz – 5 MHz integration bandwidth
Power Supply-Induced Jitter Sensitivity	PSJS	–	0.8	–	ps/mV	50 mV peak-to-peak Vdd = 3.3 V

Notes:

1. Appropriate when driving digital logic for use in setup and hold time equations.
2. Appropriate when driving phase locked loops in high-speed SerDes applications.

Table 2. Absolute Maximum Limits

Operation outside the absolute maximum ratings may cause permanent damage to the part.
Performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
Storage Temperature	-65	150	°C
Supply Voltage (Vdd)	-0.5	4	V
Electrostatic Discharge (HBM)	–	2000	V
Electrostatic Discharge (CDM)	–	750	V
Soldering Temperature (follow standard Pb free soldering guidelines)[3]	–	260	°C
Junction Temperature[4]	–	150	°C

Notes:

3. Please refer to SiTime Manufacturing Notes.
4. Exceeding this temperature for extended period of time may damage the device.

Table 3. Thermal Considerations[5]

Package	θ_{JA} (°C/W)	θ_{JB} (°C/W)	θ_{JC} (°C/W) (Top)	Ψ_{JT}(°C/W)
3225	208	76	134	15.7
2520	187	78	133	16.4
2016	190	75	167	14.9

Note:

5. θ_{JA}, Ψ_{JT}, θ_{JB} and θ_{JC} are provided according to JEDEC standards 51-2A, 51-7, 51-8, and 51-12.01 with a 25°C ambient and 250 mW power consumption (typical of 1 GHz f_{out}). The conduction thermal resistances θ_{JB} and θ_{JC} are obtained with the assumption that all heat flows from the junction to a heat sink through either the solder pads (θ_{JB}) or the top of the package ($\theta_{JC,Top}$). These may be used in a two-resistor compact model. The values of θ_{JA} and Ψ_{JT} are strongly application dependent, and we report values based on the JEDEC thermal environment. θ_{JA} is the thermal resistance to ambient on a JEDEC PCB - it is a highly conservative estimate, since the JEDEC board does not have vias to PCB planes in the vicinity of the package. Ψ_{JT} can be used to estimate the junction temperature from measurements of the temperature at the top of the package if the thermal environment is similar to the JEDEC environment.

Table 4. Maximum Operating Junction Temperature[6]

Max Operating Temperature (ambient)	Maximum Operating Junction Temperature
125°C	135°C
105°C	115°C

Note:

6. Datasheet specifications are not guaranteed if junction temperature exceeds the maximum operating junction temperature.

Table 5. Environmental Compliance

Parameter	Condition/Test Method	Value
Mechanical Shock	**MIL-STD-883F, Method 2002**	20,000 *g*
Mechanical Vibration	**MIL-STD-883F, Method 2007**	70 *g*
Vibration Fatigue	**MIL-STD-883, Method 2005, Condition A**	20 *g*
Constant Acceleration	**MIL-STD-883, Method 2001**	30,000 *g*
Temperature Cycle		JESD22, Method A104
Solderability		MIL-STD-883F, Method 2003
Moisture Sensitivity Level		MSL1 @ 260°C

Note:

7. SiT7601 is 100% screened in accordance with SiTime Endura flow.

Device Configurations and Pin-outs

Pin Description

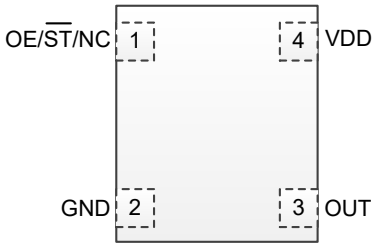


Figure 1. Pin Assignments (Top View)

Table 6. Pin Description

Pin	Symbol		Function
1	OE/ST/MS/NC	Output Enable (OE)	H[8]: specified frequency output L or Open: output is high impedance. Only output driver is disabled
		Standby (ST)	H[8]: specified frequency output L or Open: output is low (5kΩ internal pull down). Device goes into sleep mode.
		Mid-Standby (MS)	H[8]: specified frequency output L or Open: output is low (5kΩ internal pull down). Device goes into mid-standby mode
		No Connect (NC)	Any voltage between GND and Vdd or Open. Specified frequency output. Pin 1 has no function.
2	GND	Power	Electrical ground
3	OUT	Output	Oscillator output
4	VDD	Power	Power supply voltage. Place a 0.1 µF capacitor between VDD and GND, as close to the pin as possible.

Notes:

8. In OE, ST , or MS mode, a pull-up resistor of 10 kΩ or less is recommended if pin 1 is not externally driven. If pin 1 needs to be left floating, use the NC option.

Typical Performance Plots

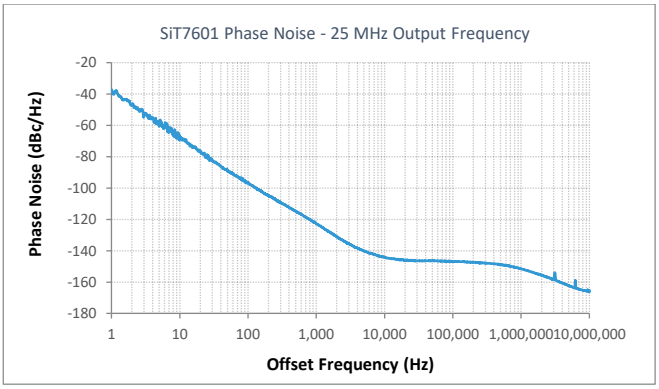


Figure 2. SiT7601 Phase Noise – 25 MHz Output Frequency

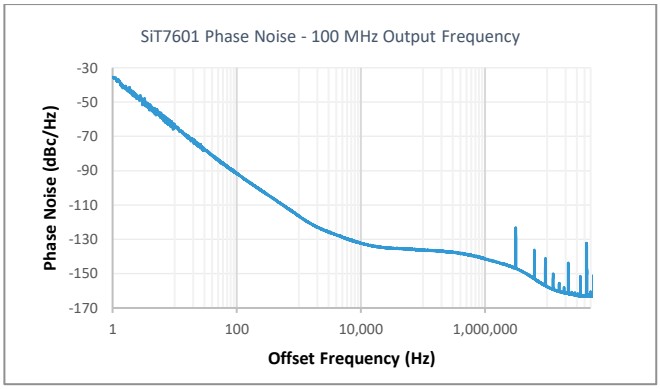


Figure 3. SiT7601 Phase Noise – 100 MHz Output Frequency

Test Circuit and Waveform

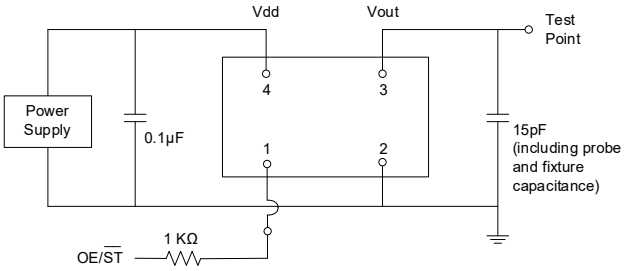


Figure 4. Test Circuit[9]

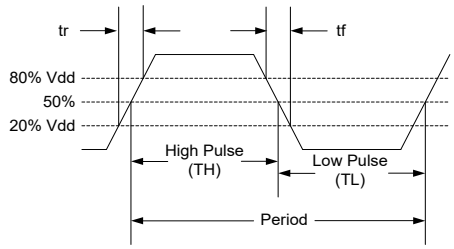


Figure 5. Waveform[9]

Note:
9. Duty Cycle is computed as Duty Cycle = TH/Period.

Timing Diagrams

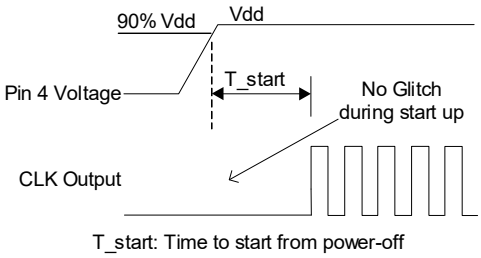


Figure 6. Startup Timing ($\overline{ST}$/ $\overline{MS}$/ NC Mode)[10]

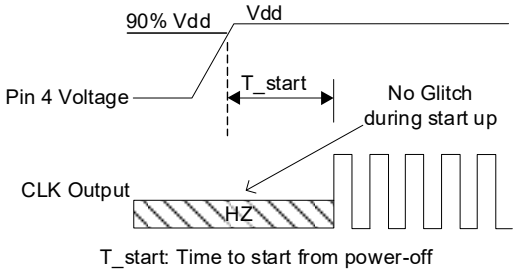


Figure 7. Startup Timing (OE Mode only)[10]

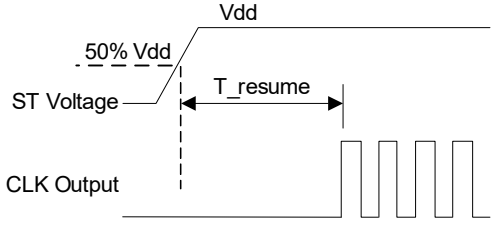


Figure 8. Standby Resume Timing ($\overline{ST}$/ $\overline{MS}$ Mode)[10]

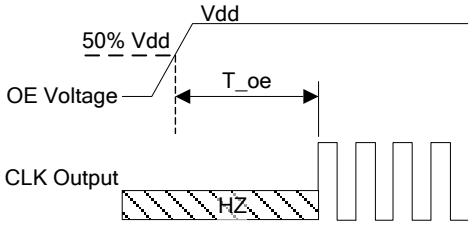


Figure 9. OE Enable Timing (OE Mode Only)

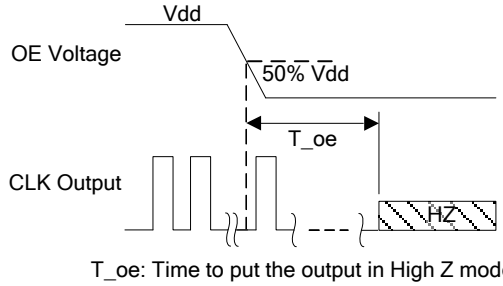


Figure 10. OE Disable Timing (OE Mode Only)

Note:
10. SiT7601 has “no runt” pulses and “no glitch” output during startup or resume.

Programmable Drive Strength

The SiT7601 includes a programmable drive strength feature to provide a simple, flexible tool to optimize the clock rise/fall time for specific applications. Benefits from the programmable drive strength feature are:

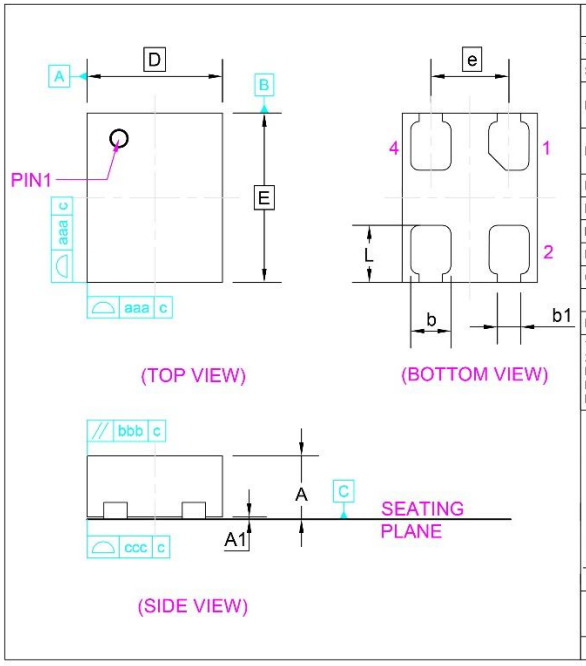
- Improves system radiated electromagnetic interference (EMI) by slowing down the clock rise/fall time.
- Improves the downstream clock receiver's (RX) jitter by decreasing (speeding up) the clock rise/fall time.
- Ability to drive large capacitive loads while maintaining full swing with sharp edge rates.

For more detailed information about rise/fall time control and drive strength selection, contact SiTime.

Dimensions and Patterns

Package Size – Dimensions (Unit: mm)[11]	Recommended Land Pattern (Unit: mm)[12]

2.0 x 1.6 x 0.75 mm

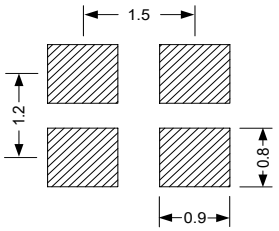


		SYMBOL	MIN	NOM	MAX
TOTAL THICKNESS		A	0.700	0.750	0.800
STAND OFF		A1	0.000	0.020	0.050
BODY SIZE	X	D		1.600 BSC	
	Y	E		2.000 BSC	
LEAD WIDTH		b	0.430	0.480	0.530
		b1	0.230	0.280	0.330
LEAD LENGTH		L	0.580	0.680	0.780
LEAD PITCH		e		0.930 BSC	
PACKAGE TOLERNCE		aaa		0.050	
MOLD FLATNESS		bbb		0.100	
COPLANARITY		ccc		0.080	

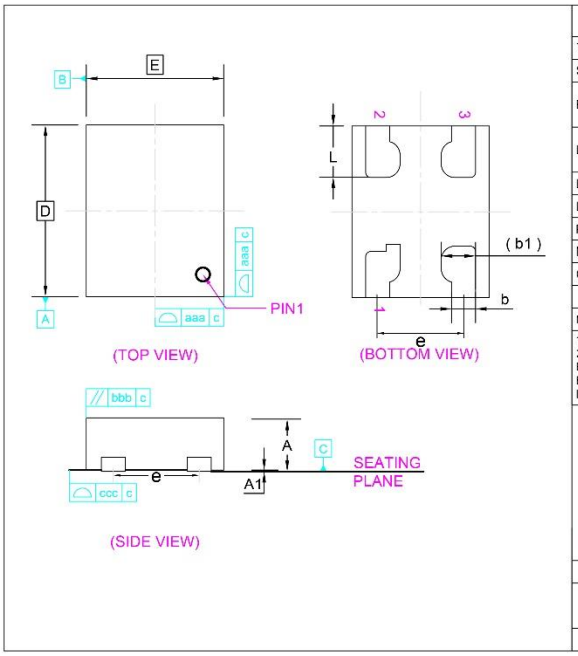
NOTE
1. ALL DIMENSION IN MM
2. BOTTOM PAD PLATING:
ELECTROLESS Ni: 10-50 µm
ELECTROLESS Pd: 0.2-0.8 µm
IMMERSION Au: 0.1-0.4 µm

SiTime

PKG INFO	DRAWING NO.
4L PQFN 1.600x2.000x0.750 mm	POD-106-PQFN-004-G02016
	REV: A01 / SHEET: 01
DATE: 8/26/2025	



2.5 x 2.0 x 0.75 mm

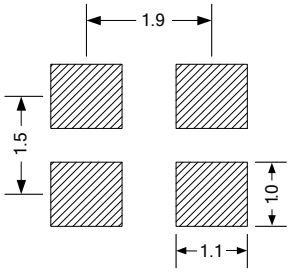


		SYMBOL	MIN	NOM	MAX
TOTAL THICKNESS		A	0.700	0.750	0.800
STAND OFF		A1	0.000	0.020	0.050
BODY SIZE	X	D		2.500 BSC	
	Y	E		2.000 BSC	
LEAD WIDTH		b	0.300	0.350	0.400
		b1	0.450	0.500	0.550
LEAD LENGTH		L	0.650	0.750	0.850
LEAD PITCH		e		1.250 BSC	
PACKAGE TOLERNCE		aaa		0.050	
MOLD FLATNESS		bbb		0.100	
COPLANARITY		ccc		0.080	

NOTE
1. ALL DIMENSION IN MM
2. BOTTOM PAD PLATING:
ELECTROLESS Ni: 10-50 µm
ELECTROLESS Pd: 0.2-0.8 µm
IMMERSION Au: 0.1-0.4 µm

SiTime

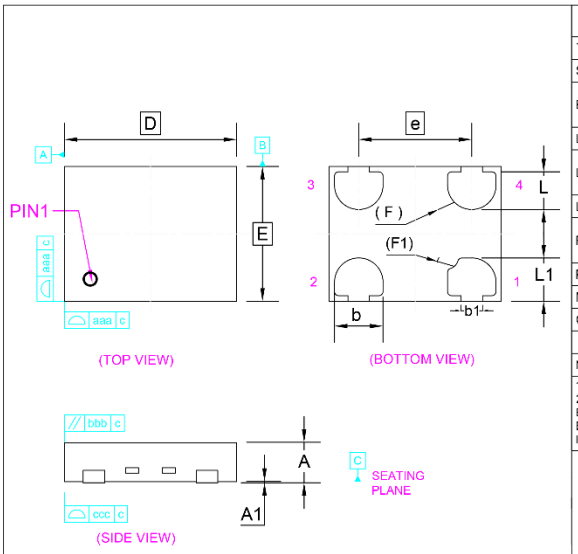
PKG INFO	DRAWING NO.
4L PQFN 2.500x2.000x0.750 mm	POD-096-PQFN-004-G02520
	REV: A02 / SHEET: 01
DATE: 8/26/2025	



Dimensions and Patterns (continued)

Package Size – Dimensions (Unit: mm)[11]	Recommended Land Pattern (Unit: mm)[12]

3.2 x 2.5 x 0.75 mm

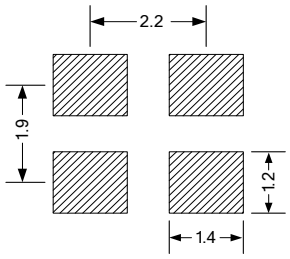


		SYMBOL	MIN	NOM	MAX
TOTAL THICKNESS		A	0.700	0.750	0.800
STAND OFF		A1	0.000	0.020	0.050
BODY SIZE	X	D		3.200 BSC	
	Y	E		2.500 BSC	
LEAD WIDTH		b	0.800	0.900	1.000
LEAD LENGTH		L	0.700	0.800	0.900
		L1	0.800	0.900	1.000
LEAD PITCH		e		2.100 BSC	
RADIUS		F		0.450 REF	
		F1		0.200 REF	
PACKAGE TOLERNCE		aaa		0.050	
MOLD FLATNESS		bbb		0.100	
COPLANARITY		ccc		0.080	

NOTE

1. ALL DIMENSION IN MM
2. BOTTOM PAD PLATING:
ELECTROLESS Ni: 10-50 µm
ELECTROLESS Pd: 0.2-0.8 µm
IMMERSION Au: 0.1-0.4 µm

PKG INFO		DRAWING NO.	
4L PQFN 3.200x2.500x0.750 mm		POD-107-PQFN-004-G03225	
		REV	SHEET
DATE	8/26/2025	A01	01

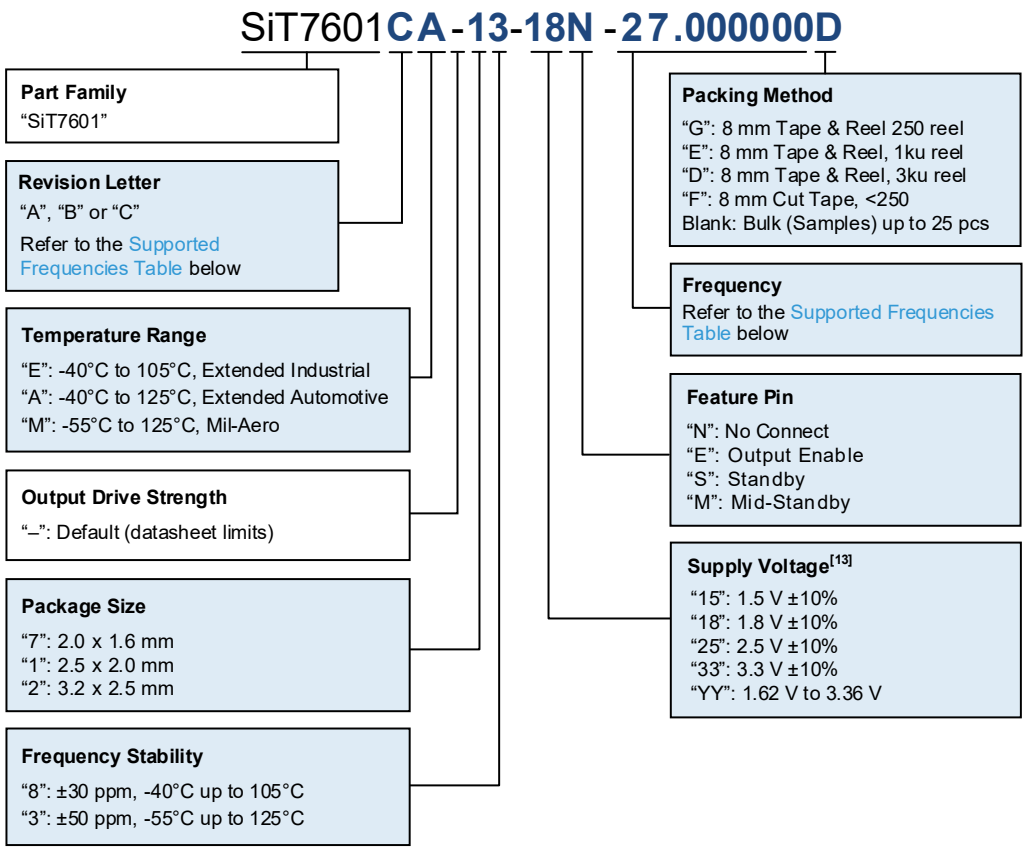


Notes:

11. Top marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device.
12. A capacitor of value 0.1 pF or higher between VDD and GND is required.

Ordering Information

The part number guide illustrated below is for reference only, in which boxes identify order codes having more than one option. To customize and build an exact part number, use the SiTime Part Number Generator. To validate the part number, use the SiTime Part Number Decoder.



Note:

13. The voltage portion of the SiT7601 part number consists of a two-digit number that denotes the specific supply voltage of the device

Table 7. Part Number and Supported Frequencies[14,15]

Frequency Range (MHz)							
SiT7601A		SiT7601B				SiT7601C	
5.000000	33.333333	4.000000	16.000000	32.000000	72.000000	7.000000	39.000000
10.000000	50.000000	4.096000	18.000000	32.768000	76.800000	13.000000	63.000000
14.74056	62.500000	6.000000	18.432000	36.000000	96.000000	21.000000	91.000000
16.93620	78.125000	8.000000	19.20000	38.400000	122.880000	27.000000	117.000000
20.000000	100.000000	8.192000	24.000000	48.000000	-	-	-
25.000000	125.000000	9.000000	24.576000	61.440000	-	-	-
31.250000	-	12.000000	30.720000	64.000000	-	-	-

Notes:

14. Any frequency the table above is supported with 6 decimal places of accuracy.
15. Please contact SiTime for frequencies that are not listed in the tables above.

Table 8. Ordering Codes for Supported Tape & Reel Packing Method

Device Size (mm x mm)	8 mm T&R (3ku)	8 mm T&R (1ku)	8 mm T&R (250u)
2.0 x 1.6	D	E	G
2.5 x 2.0	D	E	G
3.2 x 2.5	D	E	G

Instant Samples with Time Machine II and Field Programmable Oscillator

SiTime supports a field programmable version of the SiT7601 for fast prototyping and real time customization of features. The field programmable devices (FP devices) are available for all standard SiT7601 package sizes and can be configured to one's exact specification using the Time Machine II.

For more information regarding SiTime's field programmable solutions, see Time Machine II and Field Programmable devices.

SiT7601 is typically factory-programmed per customer ordering codes for volume delivery.

Additional Information

Table 9. Additional Information

Document	Description	Download Link
Time Machine II	Asterix programmer for engineering samples	http://www.sitime.com/support/time-machine-oscillator-programmer
Field Programmable Oscillators	Devices that can be programmable in the field by Time Machine II	http://www.sitime.com/products/field-programmable-oscillators
Manufacturing Notes	Tape & Reel dimension, reflow profile and other manufacturing related info	https://www.sitime.com/sites/default/files/gated/Manufacturing-Notes-for-SiTime-Products.pdf
Qualification Reports	RoHS report, reliability reports, composition reports	http://www.sitime.com/support/quality-and-reliability
Performance Reports	Additional performance data such as phase noise, current consumption, and jitter for selected frequencies	http://www.sitime.com/support/performance-measurement-report
Termination Techniques	Termination design recommendations	http://www.sitime.com/support/application-notes
Layout Techniques	Layout recommendations	http://www.sitime.com/support/application-notes

Revision History

Table 10. Revision History

Version	Release Date	Change Summary
1.0	3-Oct-2025	Initial Release
1.01	13-Oct-2025	Added “YY” Supply Voltage Option
1.02	2-Jun-2026	Update OE standby timing diagrams, added value for weak pull-down 5kΩ in Table 6 Updated Disclaimer

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